

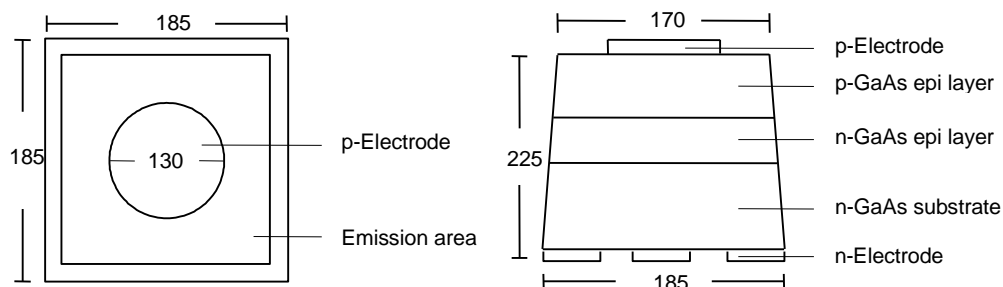
### ■ Features :

- GaAs/GaAs Wafer
- Good Spectral Matched to Si Detector

### ■ Typical Applications :

- Peripheral Device
- Photo Coupler
- Photo Interrupter

### ■ Outline Dimensions : (Unit: $\mu\text{m}$ )



### ■ Physical Structure :

Chip dimension	Chip size	185 $\mu\text{m}$ x 185 $\mu\text{m}$
	Thickness	225 $\mu\text{m}$
	Emission area	170 $\mu\text{m}$
	Bonding pad	130 $\mu\text{m}$ (110 $\mu\text{m}$ optional)
Electrode	Top: P (anode)	Aluminum
	Backside: N (cathode)	Gold alloy
Surface condition		Smooth

### ■ Electro-Optical Characteristics : ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	$V_F$	$I_F = 20 \text{ mA}$	-	1.26	1.50	V
		$I_F = 100 \text{ mA}$	-	1.48	1.90	
Reverse Voltage	$V_R$	$I_R = 10 \text{ uA}$	5	-	-	V
Wavelength	$\lambda_P$	$I_F = 20 \text{ mA}$	-	940	-	nm
Spectral width at half height	$\Delta\lambda$	$I_F = 20 \text{ mA}$	-	50	-	nm
Radiant Power	$P_o$	$I_F = 20 \text{ mA}$	0.20	-	-	mW

■ Typical Electro-Optical Characteristics Curve:

Fig 1. Forward Current vs. Forward Voltage

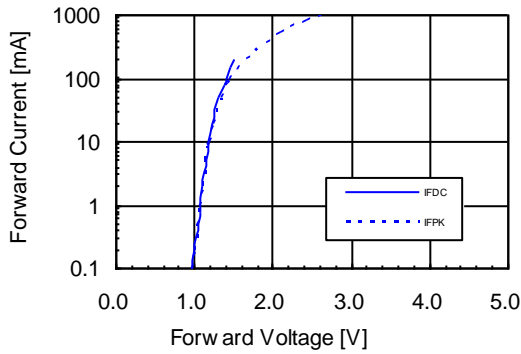


Fig 2. Relative Radiant Power vs. Wavelength

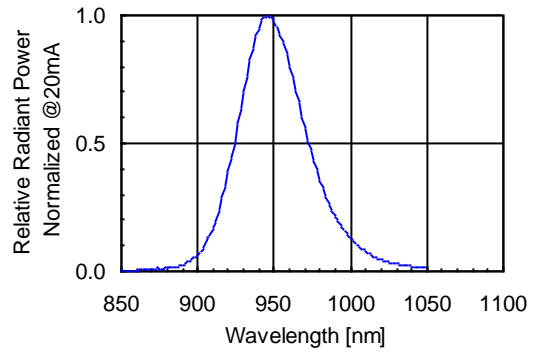


Fig 3. Relative Radiant Power vs. Forward DC Current

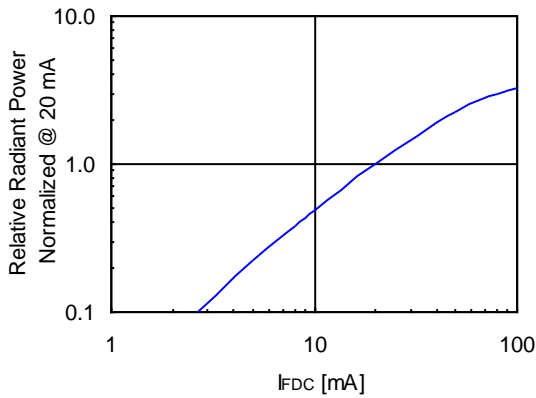


Fig 4. Relative Radiant Power vs. Forward Peak Current

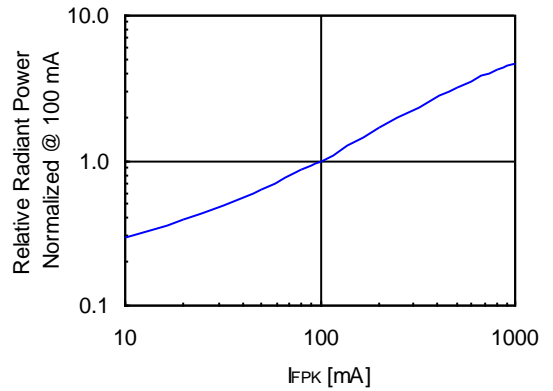


Fig 5. Forward DC Voltage vs. Temperature

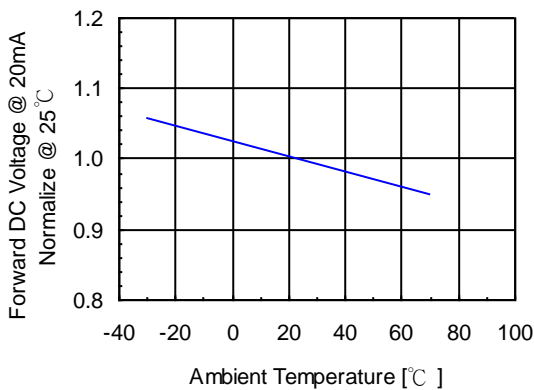


Fig 6. Relative Radiant Power vs. Temperature

